

isc Silicon NPN Power Transistors

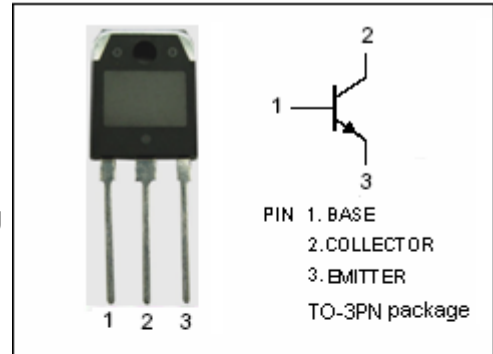
TIP52

DESCRIPTION

- DC Current Gain $-h_{FE} = 30\sim 150@ I_C = 0.3A$
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 300V(\text{Min})$

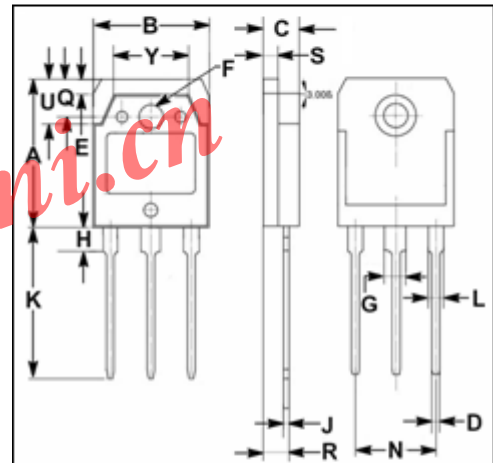
APPLICATIONS

- Designed for line operated audio output amplifier, and switching power supply drivers applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	400	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	3.0	A
I_{CM}	Collector Current-Peak	5.0	A
I_B	Base Current	0.6	A
P_D	Collector Power Dissipation $T_C=25^\circ C$	100	W
T_j	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.10
H	3.20	3.40
J	0.595	0.605
K	20.50	20.70
L	1.90	2.10
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.25	$^\circ C/W$

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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=30\text{mA}; I_B=0$	300		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.6\text{A}$		1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=3\text{A}; V_{CE}=10\text{V}$		1.5	V
I_{CES}	Collector Cutoff Current	$V_{CE}=400\text{V}; V_{BE}=0$		1.0	mA
I_{CEO}	Collector Cutoff Current	$V_{CE}=200\text{V}; I_B=0$		1.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$		1.0	mA
h_{FE-1}	DC Current Gain	$I_C=0.3\text{A}; V_{CE}=10\text{V}$	30	150	
h_{FE-2}	DC Current Gain	$I_C=3\text{A}; V_{CE}=10\text{V}$	10		
f_T	Current-Gain—Bandwidth Product	$I_C=0.2\text{A}; V_{CE}=10\text{V}$	2.5		MHz